

1. Scope

The present specifications shall apply to a FMX-22S.

2. Outline

Type	Silicon Rectifier Diode
Structure	Resin Molded Flammability: UL94V-0 (Equivalent)
Applications	High Frequency Rectification

3. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	200	
2	Peak Reverse Voltage	V_{RM}	V	200	
3	Average Forward Current	$I_{F(AV)}$	A	10	Refer to Derating of 6
4	Peak Surge Forward Current	I_{FSM}	A	65	10msec Sine wave, one shot
5	I^2t Limiting Value	I^2t	A^2s	21	$1msec \leq t \leq 10msec$
6	Junction Temperature	T_j	°C	-40~+150	
7	Storage Temperature	T_{stg}	°C	-40~+150	

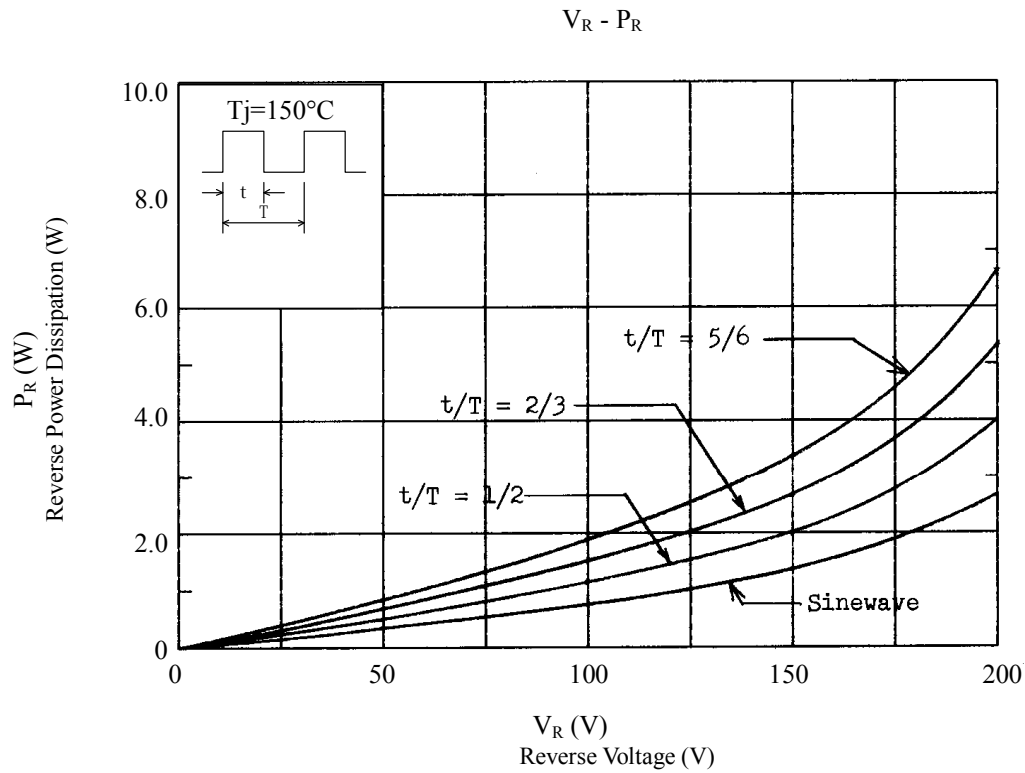
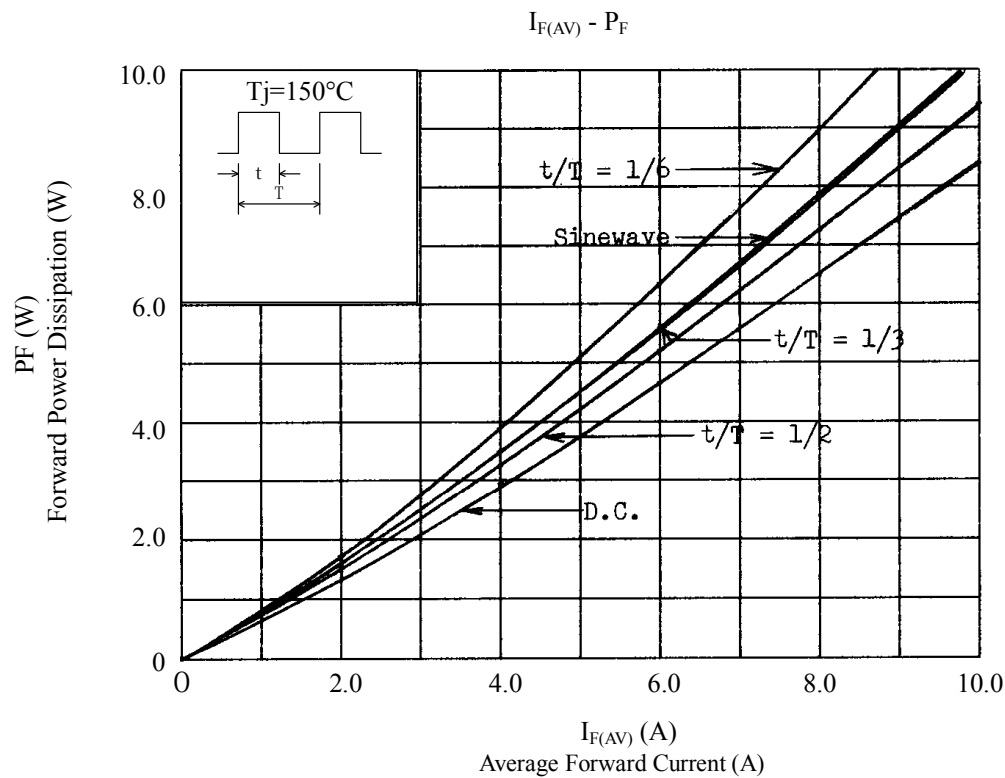
No.1,2,4&5 show ratings per one chip.

4. Electrical characteristics

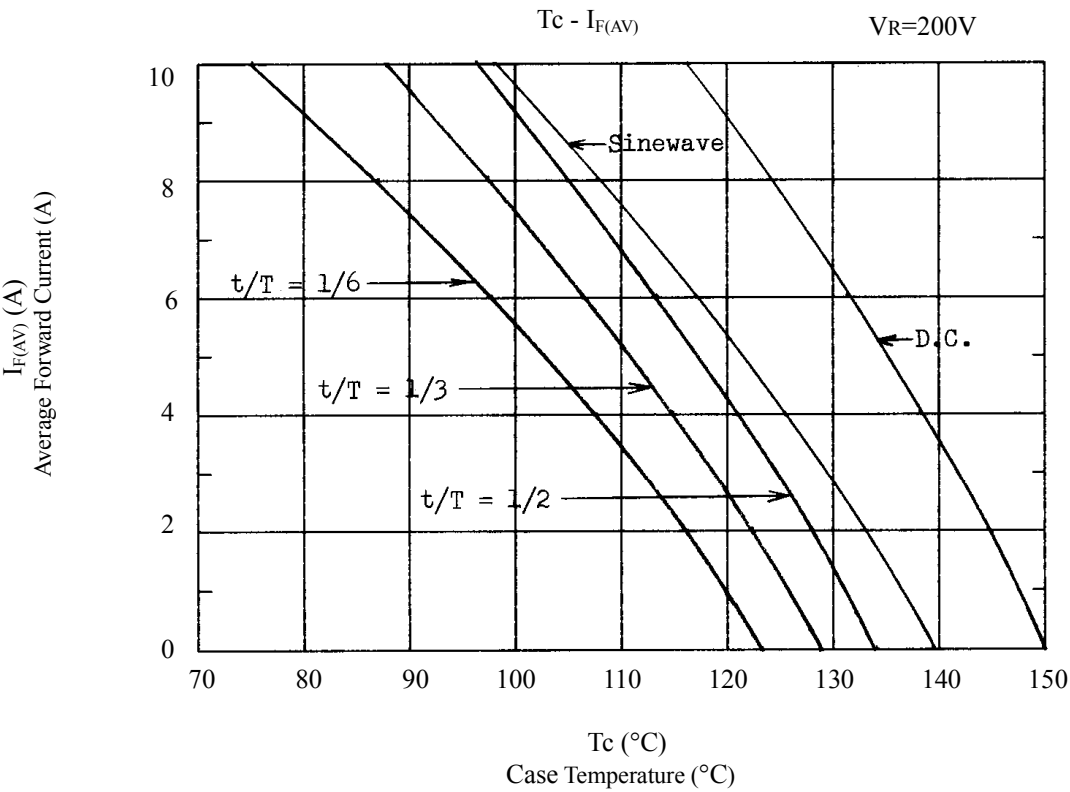
No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	0.98 max.	$I_F=5.0A$
2	Reverse Leakage Current	I_R	μA	100 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	20 max.	$V_R=V_{RM}$, $T_j=150^\circ C$
4	Reverse Recovery Time	trr1	ns	30 max.	$I_F=I_{RP}=100mA$ 90% Recovery point, $T_j=25^\circ C$
		trr2	ns	25 max.	$I_F=100mA$, $I_{RP}=200mA$, 75% Recovery point, $T_j=25^\circ C$
5	Thermal Resistance	$R_{th(j-c)}$	°C /W	4.0 max.	Between Junction and case

No.1,2,3&4 show characteristics per one chip.

5. Characteristics

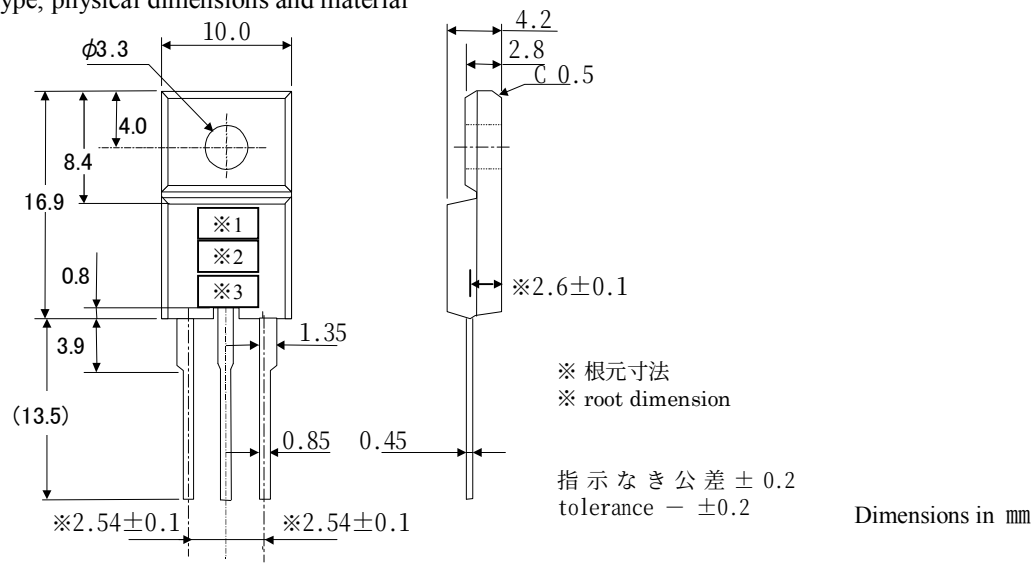


6. Derating



7. Package information

7-1 Package type, physical dimensions and material



7-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

7-3 Marking

Type Name	Marking		
	※1 Type Name	※2 Polarity	※3 Lot number
FMX-22S	FMX22S		1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 3N04 (Nov. 4, 2003)